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JOURNAL OF LUMINESCENCE

# Subject Index

Aggregation 473
Amorphous silicon 449, 455
Amorphous silicon oxide 449
Amorphous silicon-based alloy 423
Annealing 387
Anodic oxidation 173
Auger energy transfer 309
Auger excitation 375
Avalanching light-emitting diode 315

Band structure 479
Bimolecular recombination 435
Binding energy 455

Calcium fluoride 81
Cathodoluminescence 247
Chemical bonding 179
Co-evaporation 253
Cold electron emission 37
Concentration effect 395
Cross-relaxation 395

$\Delta_2$-Light hole indirect exciton 429
Deep level 343, 347
Defect 357
Defect luminescence 449
Density of state 203
Dislocation 343, 347, 467
Dye impregnated 129

Electrical measurement 391
Electroluminescence 37, 81, 91, 263, 275, 309, 315, 321, 329, 335, 405, 423, 497
Electron beam irradiation 247
Electron microscopy 257, 509
Ellipsometry 147, 183
Energy transfer 291
Epitaxial 253
Epitaxial growth 509
EPR 269
Er diffusion 303
Er-complex 9
Erbium 315
Erbium electroluminescence 375
Erbium-doped amorphous silicon 335
Er–O interaction 303
EXAFS 103, 363
Excitation/deexcitation 309
Exciton binding energy 429
Exciton diffusion 503

Fermi level 203
Fowler–Nordheim tunneling 91
Free-electron laser 291
Free-standing film 99
FT-IR 449

Ge dot 491
Ge implanted oxide 275
Ge island 515
Geminate recombination 109

High excitation effect 99
High resolution electron microscopy 223
Hot electron 309
Hot-implantation 285
Hydrogenated a-Si : H 435
Hydrogenated amorphous Si 439
Hydrosilylation 29
Hydrostatic pressure 229

Implantation 281, 357
In-plane $k$-dispersion 429
Incorporation 387
Infrared 485
Infrared absorption 241
Integrated optics 119
Interdiffusion 503
Interface roughness 129, 503
Interference filter 133
Intervalley scattering 429
Ion beam synthesis 467

Ion implantation 187, 213, 229, 235, 263, 363, 391
Ionoluminescence 187
Island 485

Laser ablation 217
Lattice location 303
LED 53, 81, 263, 381
Lewis acid 29
Light emission 213
Light emitting device 53, 405
Light emitting diode 207, 309, 329, 473, 485
Light scattering 193
Light emitting structure 335
Localized state 411
LPCVD 485
LPE 347

Magnetic resonance 297
Magnetron sputtering 241, 257
MBE 321
Memory 37
Microcavity 43, 125, 129, 137
Micropore 455
Modelling 125, 199
Molecular beam epitaxy 461
Morphology 163
Multilayer 43, 173, 423
Multiple quantum well 503
Multiquantum wells 81

Nanocluster 229, 235
Nanocomposite 115
Nanocrystal 193, 213, 235, 285
Nanocrystalline silicon 81, 253
Nanocrystalline thin film 223
Nanoparticle 519
Nanoporous 153
Nanoscale integration 53
Negative resistance 37
Non-radiative de-excitation 9

Optical absorption 257
Optical anisotropy 183
Optical band gap 65
Optical filter 173
Optical microcavity 75
Optical mode 125
Optical property 479
Optical waveguide 119, 199
Optoelectronic 363
Oxidation 99
Oxidation states of silicon 179

Passivation 169
Periodic microstructure 125
Phonon 193
Photoelectron spectroscopy 159
Photoluminescence 1, 29, 75, 99, 115, 125, 137, 153, 159, 169, 179, 213, 217, 223, 241, 253, 257, 269, 275, 339, 347, 353, 357, 363, 369, 395, 399, 417, 423, 449, 491, 497, 503, 509, 515
Photoluminescence excitation 387
Photonics 213
Photothermal laser CVD 141
Plasma CVD 247
Polarization 395
Polymer 115
Porous silicon 29, 37, 43, 53, 65, 91, 99, 103, 115, 119, 125, 129, 133, 137, 141, 147, 159, 163, 169, 173, 179, 183, 187, 193, 199, 203, 207, 339, 387, 395, 399
Pulsed-laser deposition 353

Quantum confined Stark effect 429
Quantum confinement 65, 75, 281, 411, 445
Quantum size effect 217
Quasi-direct bandgap 479

Radiative defect 281, 285
Raman scattering 241, 269
Raman spectra 179
Raman spectroscopy 223
Rapid thermal annealing 253
Rare earth impurity 391
RE ion 291
Reactive deposition epitaxy (RDE) 473
Reflectance spectrometry 163
Reflectometry 147

Sandwich structure 137
Screening 109
Self-assembled island 491
Semiconducting silicide 461
Semiconductor 1
Sensor 119
$Si/SiO_2$ superlattice 75
SiC quantum well 497
SiGe quantum well 497
Silicon cluster 223
Silicon dioxide 229
Silicon nanocluster 65, 217
Silicon nanocrystal 263
Silicon nanocrystallite 247, 269
Silicon nanograin 241, 257
Silicon nanostructure 411, 491
Silicon on insulator technology 199

Silicon p–n structure 375
SIMS 147
Solar cell 207
Sol–gel 399
Space-charge-limited-current 203
Spectroscopic ellipsometry 257
Stain etch 159
Stain etching 163
Strained SiGe 485
Strained structure 509
Superlattice 417, 439, 509
Superlinear increase 99
Template technique 461
Tensilely strained $Si_{1-y}C_y$-based QWs 429
Thin film 353, 455
Thin film alloy 405
Time-resolved PL 153
Transmission electron microscopy 369
Transport mechanism 207
Type-II interface 515

UHV evaporation 439
Ultrafast carrier dynamics 435

Visible photoluminescence 229

Waveguide 321, 329

X-ray diffraction 503
X-ray photoelectron spectroscopy 241
X-ray reflectivity 503
X-ray scattering 417
XEOL 103
XPS 159, 179, 455

ELSEVIER

Journal of Luminescence 80 (1999) 531

JOURNAL OF LUMINESCENCE

# Materials Index

a-$SiO_x$ : H 405
Alkene 29
Alkyne 29

β-$FeSi_2$ 467, 473

$CaF_2$ 253
Calcium fluoride 81

Erbium 9, 19, 297, 303, 309, 321, 329, 339, 343, 347, 353, 357, 363, 369, 381, 395, 399

Fluorine 297

Ge 275, 281

Iron disilicide 479

$Nd^{3+}$ 387

Oxygen 297, 369

Rare earth 381
Ruthenium silicide 461

Si-MBE 473
$Si/SiO_2$ layer 241, 257
SiGe 329, 485, 503, 509
SiGe alloys 153
Silica 213, 449
Silicon 1, 9, 19, 109, 159, 235, 285, 297, 303, 309, 315, 321, 329, 343, 347, 357, 363, 391, 417, 519
Silicon carbide 519
Silicon dioxide 141, 229
Silicon nitride 417
Silicon oxide 369, 369
Silicon oxide thin film 445
Silicon–germanium 381
SiN 339
$SiO_2$ 275, 281, 285
$SiO_2$ : Er 353